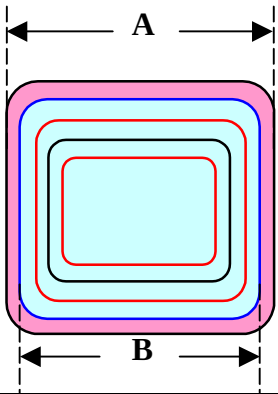


Features : * Extremely low forward volts * Guard ring protection * Low reverse leakage current 	Chip size(A):		1.016 * 1.016 mm ²
	Bond Pad size(B) :		0.889 * 0.889 mm ²
	Thickness :		300μm ± 20μm
	Metalization :		Anode Ti/Ni/Ag
	Metalization :		Cathode Ti/Ni/Ag
Electrical Characteristics	Sym.	Spec. Limit	Unit
Maximum Instantaneous Forward Volt at IF : 1.0Amp. 25°C	VF max	0.48	Volt
Minimum Instantaneous Reverse Voltage at IR : 200 uA 25°C	VR min.	43	Volt.
Minimum Non-repetitive Peak Surge current at 25°C	IFSM	40	Amp
Storage Temperature	TSTG	-65 to +125	°C

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